

RoHS

Lxx08xx & Qxx08xx & Qxx08xHx Series



Description

8 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed and temperature modulation controls, lighting controls, and static switching relays.

Sensitive type devices guarantee gate control in Quadrants I & IV needed for digital control circuitry.

Standard type devices normally operate in Quadrants I & III triggered from AC line.

Alternistor type devices only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

Agency Approval

| Agency | Agency File Number |
|--------|--------------------|
| | L Package: E71639 |

Main Features

| Symbol | Value | Unit |
|-------------------|-------------|------|
| $I_{T(RMS)}$ | 8 | A |
| V_{DRM}/V_{RRM} | 400 to 1000 | V |
| $I_{GT(Q1)}$ | 5 to 50 | mA |

Schematic Symbol



Features & Benefits

- RoHS compliant
- Glass – passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 100 A
- Electrically isolated “L-Package” is UL recognized for 2500Vrms
- Solid-state switching eliminates arcing or contact bounce that create voltage transients
- No contacts to wear out from reaction of switching events
- Restricted (or limited) RFI generation, depending on activation point of sine wave
- Requires only a small gate activation pulse in each half-cycle

Applications

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, light dimmers, power tools, home/brown goods and white goods appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Absolute Maximum Ratings — Sensitive Triac (4 Quadrants)

| Symbol | Parameter | | Value | Unit | |
|--------------|--------------------------------------------------------------------------------------------------|-----------------------------|---------------------------|------------|------------------------|
| $I_{T(RMS)}$ | RMS on-state current (full sine wave) | Lxx08Ly | $T_C = 80^\circ\text{C}$ | 8 | A |
| | | Lxx08Ry / Lxx08Vy / Lxx08Dy | $T_C = 85^\circ\text{C}$ | | |
| I_{TSM} | Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C) | f = 50 Hz | t = 20 ms | 65 | A |
| | | f = 60 Hz | t = 16.7 ms | 85 | |
| I^2t | I^2t Value for fusing | $t_p = 8.3$ ms | | 26.5 | A^2s |
| di/dt | Critical rate of rise of on-state current $I_G = 50\text{mA}$ with $0.1\mu\text{s}$ rise time | f = 120 Hz | $T_J = 110^\circ\text{C}$ | 70 | $\text{A}/\mu\text{s}$ |
| I_{GTM} | Peak gate trigger current | $t_p \leq 10 \mu\text{s}$ | $T_J = 110^\circ\text{C}$ | 1.6 | A |
| $P_{G(AV)}$ | Average gate power dissipation | $T_J = 110^\circ\text{C}$ | | 0.4 | W |
| T_{stg} | Storage temperature range | | | -40 to 150 | $^\circ\text{C}$ |
| T_J | Operating junction temperature range | | | -40 to 110 | $^\circ\text{C}$ |

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Standard Triac

| Symbol | Parameter | | Value | Unit | |
|--------------|--------------------------------------------------------------------------------------------------------|-----------------------------------------------------|---------------------------|------------|------------------------|
| $I_{T(RMS)}$ | RMS on-state current (full sine wave) | Qxx08Ry / Qxx08Ny | $T_C = 95^\circ\text{C}$ | 8 | A |
| | | Qxx08Ly | $T_C = 90^\circ\text{C}$ | | |
| I_{TSM} | Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C) | f = 50 Hz | t = 20 ms | 83 | A |
| | | f = 60 Hz | t = 16.7 ms | 100 | |
| I^2t | I^2t Value for fusing | $t_p = 8.3$ ms | | 41 | A^2s |
| di/dt | Critical rate of rise of on-state current $I_G = 200\text{mA}$ with $\leq 0.1\mu\text{s}$ rise time | f = 120 Hz | $T_J = 125^\circ\text{C}$ | 70 | $\text{A}/\mu\text{s}$ |
| I_{GTM} | Peak gate trigger current | $t_p \leq 10 \mu\text{s};$ $I_{GT} \leq I_{GTM}$ | $T_J = 125^\circ\text{C}$ | 1.8 | A |
| $P_{G(AV)}$ | Average gate power dissipation | $T_J = 125^\circ\text{C}$ | | 0.5 | W |
| T_{stg} | Storage temperature range | | | -40 to 150 | $^\circ\text{C}$ |
| T_J | Operating junction temperature range | | | -40 to 125 | $^\circ\text{C}$ |

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Alternistor (3 Quadrants)

| Symbol | Parameter | | Value | Unit | | |
|--------------|-------------------------------------------------------------------------------------------------|-----------------------------------------------------|--------------------------------------|--------------------------------------|----------------------|---|
| $I_{T(RMS)}$ | RMS on-state current (full sine wave) | Qxx08LHy | $T_C = 90^\circ\text{C}$ | 8 | A | |
| | | Qxx08RHy / Qxx08NHy Qxx08VHy / Qxx08DHy | $T_C = 95^\circ\text{C}$ | | | |
| I_{TSM} | Non repetitive surge peak on-state current (full cycle, T_J initial = 25°C) | f = 50 Hz | t = 20 ms | Qxx08VHy / Qxx08DHy | 80 | A |
| | | | | Qxx08LHy / Qxx08RHy / Qxx08NHy | 83 | |
| | | f = 60 Hz | t = 16.7 ms | Qxx08VHy / Qxx08DHy | 85 | |
| | | | | Qxx08LHy / Qxx08RHy / Qxx08NHy | 100 | |
| I^2t | I^2t Value for fusing | $t_p = 8.3$ ms | Qxx08VHy / Qxx08DHy | 30 | A^2s | |
| | | | Qxx08LHy / Qxx08RHy / Qxx08NHy | 41 | | |
| di/dt | Critical rate of rise of on-state current | f = 120 Hz | $T_J = 125^\circ\text{C}$ | 70 | A/ μs | |
| I_{GTM} | Peak gate trigger current | $t_p \leq 10 \mu\text{s};$ $I_{GT} \leq I_{GTM}$ | $T_J = 125^\circ\text{C}$ | Qxx08VHy / Qxx08DHy | 1.6 | A |
| | | | | Qxx08LHy / Qxx08RHy / Qxx08NHy | 2.0 | |
| $P_{G(AV)}$ | Average gate power dissipation | $T_J = 125^\circ\text{C}$ | $I_{GT} = 10\text{mA}$ | Qxx08VHy / Qxx08DHy | 0.4 | W |
| | | | $I_{GT} = 35\text{mA}$ | Qxx08LHy / Qxx08RHy / Qxx08NHy | 0.5 | |
| T_{stg} | Storage temperature range | | | -40 to 150 | $^\circ\text{C}$ | |
| T_J | Operating junction temperature range | | | -40 to 125 | $^\circ\text{C}$ | |

Note: xx = voltage, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Sensitive Triac (4 Quadrants)

| Symbol | Test Conditions | Quadrant | | Lxx08x6 | Lxx08x8 | Unit |
|----------|-----------------------------------------------------------------------|--------------------|------|---------|----------|------------------|
| I_{GT} | $V_D = 12\text{V}$ $R_L = 60 \Omega$ | I – II – III IV | MAX. | 5 10 | 10 20 | mA |
| V_{GT} | | ALL | MAX. | 1.3 | | V |
| V_{GD} | $V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_J = 110^\circ\text{C}$ | ALL | MIN. | 0.2 | | V |
| I_H | $I_T = 100\text{mA}$ | | MAX. | 10 | 20 | mA |
| dv/dt | $V_D = V_{DRM}$ Gate Open $T_J = 100^\circ\text{C}$ | 400V | TYP. | 30 | 40 | V/ μs |
| | | 600V | | 20 | 30 | |
| (dv/dt)c | (di/dt)c = 4.3 A/ms $T_J = 110^\circ\text{C}$ | | TYP. | 2 | 2 | V/ μs |
| t_{gt} | $I_G = 100\text{mA}$ $PW = 15\mu\text{s}$ $I_T = 11.3 \text{ A(pk)}$ | | TYP. | 3.0 | 3.2 | μs |

Note: xx = voltage, x = package, y = sensitivity

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Standard Triac

| Symbol | Test Conditions | Quadrant | | Qxx08x4 | Qxx08x5 | Unit |
|----------|-----------------------------------------------------------------------|--------------------|--------------|----------|----------|------------------|
| I_{GT} | $V_D = 12\text{V}$ $R_L = 60\ \Omega$ | I – II – III IV | MAX. TYP. | 25 50 | 50 75 | mA |
| V_{GT} | | I – II – III | MAX. | 1.3 | | V |
| V_{GD} | $V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_J = 125^\circ\text{C}$ | ALL | MIN. | 0.2 | | V |
| I_H | $I_T = 200\text{mA}$ | | MAX. | 50 | 50 | mA |
| dv/dt | $V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$ | 400V | MIN. | 150 | | V/ μs |
| | | 600V | | | 125 | |
| | | 800V | | | 100 | |
| | | 1000V | | | 80 | |
| (dv/dt)c | (di/dt)c = 4.3 A/ms $T_J = 125^\circ\text{C}$ | | TYP. | 4 | 4 | V/ μs |
| t_{gt} | $I_G = 100\text{mA}$ $PW = 15\mu\text{s}$ $I_T = 11.3\ \text{A(pk)}$ | | TYP. | 3.0 | 3.0 | μs |

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise specified) — Alternistor Triac (3 Quadrants)

| Symbol | Test Conditions | Quadrant | | | Qxx08xH3 | Qxx08xH4 | Unit |
|----------|-----------------------------------------------------------------------|--------------------------------------------------------------|------|-------|----------|----------|------------------|
| I_{GT} | $V_D = 12\text{V}$ $R_L = 60\ \Omega$ | I – II – III | MAX. | | 10 | 35 | mA |
| V_{GT} | | I – II – III | MAX. | | 1.3 | | V |
| V_{GD} | $V_D = V_{DRM}$ $R_L = 3.3\ \text{k}\Omega$ $T_J = 125^\circ\text{C}$ | I – II – III | MIN. | | 0.2 | | V |
| I_H | $I_T = 100\text{mA}$ | | MAX. | | 15 | 35 | mA |
| dv/dt | $V_D = V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$ | Qxx08LHy / Qxx08RH _y / Qxx08NH _y | MIN. | 400V | 75 | 400 | V/ μs |
| | | | | 600V | 50 | 300 | |
| | | | | 800V | | 200 | |
| | | | | 1000V | | 100 | |
| | | Qxx08VHy / Qxx08DH _y | | 400V | 75 | 450 | |
| | | | | 600V | 50 | 350 | |
| | | | | 800V | | 250 | |
| | | | | 1000V | | 150 | |
| (dv/dt)c | (di/dt)c = 4.3 A/ms $T_J = 125^\circ\text{C}$ | | MIN. | | 20 | 25 | V/ μs |
| t_{gt} | $I_G = 100\text{mA}$ $PW = 15\mu\text{s}$ $I_T = 11.3\ \text{A(pk)}$ | | TYP. | | 4.0 | 4.0 | μs |

Note : xx = voltage, x = package, y = sensitivity

Static Characteristics

| Symbol | Test Conditions | | | Value | Unit | |
|------------------------|------------------------------------|----------|---------------------|-------------|--------|------------|
| V_{TM} | $I_{TM} = 11.3A$ $t_p = 380 \mu s$ | | | MAX. | 1.60 V | |
| I_{DRM} I_{RRM} | $V_{DRM} = V_{RRM}$ | Lxx08xy | $T_J = 25^\circ C$ | 400 - 600V | MAX. | 20 μA |
| | | | $T_J = 110^\circ C$ | 400 - 600V | | 0.5 mA |
| | | Qxx08xy | $T_J = 25^\circ C$ | 400 - 1000V | | 50 μA |
| | | | $T_J = 125^\circ C$ | 400 - 800V | | 2 mA |
| | | | $T_J = 100^\circ C$ | 1000V | | 3 mA |
| | | Qxx08xHy | $T_J = 25^\circ C$ | 400 - 800V | | 10 μA |
| | | | | 1000V | | 20 μA |
| | | | $T_J = 125^\circ C$ | 400 - 800V | | 2 mA |
| | | | $T_J = 100^\circ C$ | 1000V | | 3 mA |

Thermal Resistances

| Symbol | Parameter | Value | Unit |
|-------------------|-----------------------|-------------------------|------|
| $R_{\theta(J-C)}$ | Junction to case (AC) | L/Qxx08Ryy / L/Qxx08Nyy | 1.5 |
| | | L/Qxx08Lyy | 2.8 |
| | | L/Qxx08Vyy | 2.1 |
| $R_{\theta(J-A)}$ | Junction to ambient | L/Qxx08Ryy | 45 |
| | | L/Qxx08Lyy | 50 |
| | | L/Qxx08Vyy | 64 |

Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

Figure 1: Definition of Quadrants



Figure 2: Normalized DC Gate Trigger Current for All Quadrants vs. Junction Temperature



Figure 3: Normalized DC Holding Current vs. Junction Temperature



Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature



Figure 5: Power Dissipation (Typical) vs. RMS On-State Current



Figure 6: Maximum Allowable Case Temperature vs. On-State Current (Sensitive Triac)



Figure 7: Maximum Allowable Case Temperature vs. On-State Current (Standard / Alternistor Triac)



Figure 8: On-State Current vs. On-State Voltage (Typical)



Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

Figure 9: Maximum Allowable Ambient Temperature vs. On-State Current



Figure 10: Surge Peak On-State Current vs. Number of Cycles



SUPPLY FREQUENCY: 60 Hz Sinusoidal
LOAD: Resistive
RMS On-State Current: $I_{T(RMS)}$: Maximum Rated Value at Specified Case Temperature

Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

Soldering Parameters

| | | |
|--------------------------------------------------------|------------------------------------|-------------------------|
| Reflow Condition | | Pb – Free assembly |
| Pre Heat | - Temperature Min ($T_{s(min)}$) | 150°C |
| | - Temperature Max ($T_{s(max)}$) | 200°C |
| | - Time (min to max) (t_s) | 60 – 180 secs |
| Average ramp up rate (Liquidus Temp (T_L) to peak) | | 5°C/second max |
| $T_{s(max)}$ to T_L - Ramp-up Rate | | 5°C/second max |
| Reflow | - Temperature (T_L) (Liquidus) | 217°C |
| | - Temperature (t_L) | 60 – 150 seconds |
| Peak Temperature (T_p) | | 260 ^{+0/-5} °C |
| Time within 5°C of actual peak Temperature (t_p) | | 20 – 40 seconds |
| Ramp-down Rate | | 5°C/second max |
| Time 25°C to peak Temperature (T_p) | | 8 minutes Max. |
| Do not exceed | | 280°C |



Physical Specifications

| | |
|--------------------------|---------------------------------------------------------------|
| Terminal Finish | 100% Matte Tin-plated |
| Body Material | UL recognized epoxy meeting flammability classification 94V-0 |
| Terminal Material | Copper Alloy |

Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

| Test | Specifications and Conditions |
|-------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------|
| AC Blocking (V_{DRM}) | MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours |
| Temperature Cycling | MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time |
| Temperature/Humidity | EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity |
| High Temp Storage | MIL-STD-750, M-1031, 1008 hours; 150°C |
| Low-Temp Storage | 1008 hours; -40°C |
| Thermal Shock | MIL-STD-750, M-1056 10 cycles; 0°C to 100°C; 5-min dwell-time at each temperature; 10 sec (max) transfer time between temperature |
| Autoclave | EIA / JEDEC, JESD22-A102 168 hours (121°C at 2 ATMs) and 100% R/H |
| Resistance to Solder Heat | MIL-STD-750 Method 2031 |
| Solderability | ANSI/J-STD-002, category 3, Test A |
| Lead Bend | MIL-STD-750, M-2036 Cond E |

Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



| Dimension | Inches | | Millimeters | |
|-----------|--------|-------|-------------|-------|
| | Min | Max | Min | Max |
| A | 0.380 | 0.420 | 9.65 | 10.67 |
| B | 0.105 | 0.115 | 2.67 | 2.92 |
| C | 0.230 | 0.250 | 5.84 | 6.35 |
| D | 0.590 | 0.620 | 14.99 | 15.75 |
| E | 0.142 | 0.147 | 3.61 | 3.73 |
| F | 0.110 | 0.130 | 2.79 | 3.30 |
| G | 0.540 | 0.575 | 13.72 | 14.61 |
| H | 0.025 | 0.035 | 0.64 | 0.89 |
| J | 0.195 | 0.205 | 4.95 | 5.21 |
| K | 0.095 | 0.105 | 2.41 | 2.67 |
| L | 0.060 | 0.075 | 1.52 | 1.91 |
| M | 0.085 | 0.095 | 2.16 | 2.41 |
| N | 0.018 | 0.024 | 0.46 | 0.61 |
| O | 0.178 | 0.188 | 4.52 | 4.78 |
| P | 0.045 | 0.060 | 1.14 | 1.52 |
| R | 0.038 | 0.048 | 0.97 | 1.22 |

Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



| Dimension | Inches | | Millimeters | |
|-----------|--------|-------|-------------|-------|
| | Min | Max | Min | Max |
| A | 0.380 | 0.420 | 9.65 | 10.67 |
| B | 0.105 | 0.115 | 2.67 | 2.92 |
| C | 0.230 | 0.250 | 5.84 | 6.35 |
| D | 0.590 | 0.620 | 14.99 | 15.75 |
| E | 0.142 | 0.147 | 3.61 | 3.73 |
| F | 0.110 | 0.130 | 2.79 | 3.30 |
| G | 0.540 | 0.575 | 13.72 | 14.61 |
| H | 0.025 | 0.035 | 0.64 | 0.89 |
| J | 0.195 | 0.205 | 4.95 | 5.21 |
| K | 0.095 | 0.105 | 2.41 | 2.67 |
| L | 0.060 | 0.075 | 1.52 | 1.91 |
| M | 0.085 | 0.095 | 2.16 | 2.41 |
| N | 0.018 | 0.024 | 0.46 | 0.61 |
| O | 0.178 | 0.188 | 4.52 | 4.78 |
| P | 0.045 | 0.060 | 1.14 | 1.52 |
| R | 0.038 | 0.048 | 0.97 | 1.22 |

Dimensions — TO-263AB (N-Package) — D²-PAK Surface Mount



| Dimension | Inches | | Millimeters | |
|-----------|--------|-------|-------------|-------|
| | Min | Max | Min | Max |
| A | 0.360 | 0.370 | 9.14 | 9.40 |
| B | 0.380 | 0.420 | 9.65 | 10.67 |
| C | 0.178 | 0.188 | 4.52 | 4.78 |
| D | 0.025 | 0.035 | 0.64 | 0.89 |
| E | 0.045 | 0.060 | 1.14 | 1.52 |
| F | 0.060 | 0.075 | 1.52 | 1.91 |
| G | 0.095 | 0.105 | 2.41 | 2.67 |
| H | 0.092 | 0.102 | 2.34 | 2.59 |
| J | 0.018 | 0.024 | 0.46 | 0.61 |
| K | 0.090 | 0.110 | 2.29 | 2.79 |
| S | 0.590 | 0.625 | 14.99 | 15.88 |
| V | 0.035 | 0.045 | 0.89 | 1.14 |
| U | 0.002 | 0.010 | 0.05 | 0.25 |
| W | 0.040 | 0.070 | 1.02 | 1.78 |

Dimensions — TO-251AA (V-Package) — V-PAK Through Hole



| Dimension | Inches | | | Millimeters | | |
|-----------|--------|-------|-------|-------------|------|------|
| | Min | Typ | Max | Min | Typ | Max |
| A | 0.040 | 0.044 | 0.050 | 1.02 | 1.11 | 1.27 |
| B | 0.235 | 0.242 | 0.245 | 5.97 | 6.15 | 6.22 |
| C | 0.350 | 0.361 | 0.375 | 8.89 | 9.18 | 9.53 |
| D | 0.205 | 0.208 | 0.213 | 5.21 | 5.29 | 5.41 |
| E | 0.255 | 0.262 | 0.265 | 6.48 | 6.66 | 6.73 |
| F | 0.027 | 0.031 | 0.033 | 0.69 | 0.80 | 0.84 |
| G | 0.087 | 0.090 | 0.093 | 2.21 | 2.28 | 2.36 |
| H | 0.085 | 0.092 | 0.095 | 2.16 | 2.34 | 2.41 |
| I | 0.176 | 0.180 | 0.184 | 4.47 | 4.57 | 4.67 |
| J | 0.018 | 0.020 | 0.023 | 0.46 | 0.51 | 0.58 |
| K | 0.038 | 0.040 | 0.044 | 0.97 | 1.01 | 1.12 |
| L | 0.018 | 0.020 | 0.023 | 0.46 | 0.52 | 0.58 |
| P | 0.042 | 0.047 | 0.052 | 1.06 | 1.20 | 1.32 |
| Q | 0.034 | 0.039 | 0.044 | 0.86 | 1.00 | 1.11 |
| R | 0.034 | 0.039 | 0.044 | 0.86 | 1.00 | 1.11 |
| S | 0.074 | 0.079 | 0.084 | 1.86 | 2.00 | 2.11 |

Dimensions — TO-252AA (D-Package) — D-PAK Surface Mount



| Dimension | Inches | | | Millimeters | | |
|-----------|--------|-------|-------|-------------|------|------|
| | Min | Typ | Max | Min | Typ | Max |
| A | 0.040 | 0.043 | 0.050 | 1.02 | 1.09 | 1.27 |
| B | 0.235 | 0.243 | 0.245 | 5.97 | 6.16 | 6.22 |
| C | 0.106 | 0.108 | 0.113 | 2.69 | 2.74 | 2.87 |
| D | 0.205 | 0.208 | 0.213 | 5.21 | 5.29 | 5.41 |
| E | 0.255 | 0.262 | 0.265 | 6.48 | 6.65 | 6.73 |
| F | 0.027 | 0.031 | 0.033 | 0.69 | 0.80 | 0.84 |
| G | 0.087 | 0.090 | 0.093 | 2.21 | 2.28 | 2.36 |
| H | 0.085 | 0.092 | 0.095 | 2.16 | 2.33 | 2.41 |
| I | 0.176 | 0.179 | 0.184 | 4.47 | 4.55 | 4.67 |
| J | 0.018 | 0.020 | 0.023 | 0.46 | 0.51 | 0.58 |
| K | 0.038 | 0.040 | 0.044 | 0.97 | 1.02 | 1.12 |
| L | 0.018 | 0.020 | 0.023 | 0.46 | 0.51 | 0.58 |
| M | 0.000 | 0.000 | 0.004 | 0.00 | 0.00 | 0.10 |
| N | 0.021 | 0.026 | 0.027 | 0.53 | 0.67 | 0.69 |
| O | 0° | 0° | 5° | 0° | 0° | 5° |
| P | 0.042 | 0.047 | 0.052 | 1.06 | 1.20 | 1.32 |
| Q | 0.034 | 0.039 | 0.044 | 0.86 | 1.00 | 1.11 |

Product Selector

| Part Number | Voltage (xx) | | | | Gate Sensitivity Quadrants | | Type | Package |
|-------------|--------------|------|------|-------|----------------------------|-------|-------------------|----------------------------|
| | 400V | 600V | 800V | 1000V | I – II – III | IV | | |
| Lxx08L6 | X | X | | | 5 mA | 10 mA | Sensitive Triac | TO-220L |
| Lxx08D6 | X | X | | | 5 mA | 10 mA | Sensitive Triac | TO-252 D-PAK |
| Lxx08R6 | X | X | | | 5mA | 10mA | Sensitive Triac | TO-220R |
| Lxx08V6 | X | X | | | 5 mA | 10 mA | Sensitive Triac | TO-251 V-PAK |
| Lxx08L8 | X | X | | | 10 mA | 20 mA | Sensitive Triac | TO-220L |
| Lxx08D8 | X | X | | | 10 mA | 20 mA | Sensitive Triac | TO-252 D-PAK |
| Lxx08R8 | X | X | | | 10mA | 20mA | Sensitive Triac | TO-220R |
| Lxx08V8 | X | X | | | 10 mA | 20 mA | Sensitive Triac | TO-251 V-PAK |
| Qxx08RH3 | X | X | | | 10 mA | | Alternistor Triac | TO-220R |
| Qxx08VH3 | X | X | | | 10 mA | | Alternistor Triac | TO-251 V-PAK |
| Qxx08DH3 | X | X | | | 10 mA | | Alternistor Triac | TO-252 D-PAK |
| Qxx08L4 | X | | | | 25 mA | | Triac | TO-220L |
| Qxx08R4 | X | | | | 25 mA | | Triac | TO-220R |
| Qxx08N4 | X | | | | 25 mA | | Triac | TO-263 D ² -PAK |
| Qxx08LH4 | X | X | X | X | 35 mA | | Alternistor Triac | TO-220L |
| Qxx08RH4 | X | X | X | X | 35 mA | | Alternistor Triac | TO-220R |
| Qxx08VH4 | X | X | X | X | 35 mA | | Alternistor Triac | TO-251 V-PAK |
| Qxx08DH4 | X | X | X | X | 35 mA | | Alternistor Triac | TO-252 D-PAK |
| Qxx08NH4 | X | X | X | X | 35 mA | | Alternistor Triac | TO-263 D ² -PAK |
| Qxx08L5 | | X | X | X | 50 mA | | Triac | TO-220L |
| Qxx08R5 | | X | X | X | 50 mA | | Triac | TO-220R |
| Qxx08N5 | | X | X | X | 50 mA | | Triac | TO-263 D ² -PAK |

Packing Options

| Part Number | Marking | Weight | Packing Mode | Base Quantity |
|----------------|--------------|--------|------------------|-------------------|
| L/Qxx08L/Ryy | L/Qxx08L/Ryy | 2.2 g | Bulk | 500 |
| L/Qxx08L/RyyTP | L/Qxx08L/Ryy | 2.2 g | Tube Pack | 500 (50 per tube) |
| Qxx08NyyTP | Qxx08Nyy | 1.6 g | Tube | 500 (50 per tube) |
| Qxx08NyyRP | Qxx08Nyy | 1.6 g | Embossed Carrier | 500 |
| L/Qxx08DyyTP | L/Qxx08Dyy | 0.3 g | Tube | 750 (75 per tube) |
| L/Qxx08DyyRP | L/Qxx08Dyy | 0.3 g | Embossed Carrier | 2500 |
| L/Qxx08VyyTP | L/Qxx08Vyy | 0.4 g | Tube | 750 (75 per tube) |

Note: xx = voltage, x = package, y = sensitivity, yy = type & sensitivity

TO-252 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards



TO-263 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards



Part Numbering System

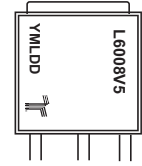


Part Marking System

TO-220 AB – (R Package)
 TO-263 AB – (N Package)



TO-252AA – (D Package)
 TO-251AA – (V Package)



TO-220 AB – (L Package)



Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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